

Data Sheet January 2000 File Number 3413.3

# 75A, 1200V Ultrafast Diode

The RURU75120 is an ultrafast diode with soft recovery characteristics ( $t_{rr}$  < 125ns). It has low forward voltage drop and is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristic minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA49032.

## **Ordering Information**

PART NUMBER	PACKAGE	BRAND
RURU75120	TO-218	RURU75120

NOTE: When ordering, use the entire part number.

## Symbol



#### **Features**

•	Ultrafast with Soft Recovery <125ns
•	Operating Temperature
•	Reverse Voltage

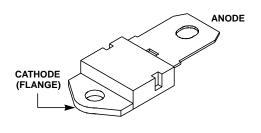
- Avalanche Energy Rated
- Planar Construction

## **Applications**

- · Switching Power Supplies
- · Power Switching Circuits
- · General Purpose

#### **Packaging**

**JEDEC STYLE SINGLE LEAD TO-218** 



#### **Absolute Maximum Ratings** $T_C = 25^{\circ}C$

	RURU75120	UNITS
Peak Repetitive Reverse VoltageV <sub>RRM</sub>	1200	V
Working Peak Reverse Voltage	1200	V
DC Blocking VoltageV <sub>R</sub>	1200	V
Average Rectified Forward Current	75	Α
$(T_C = 57^{\circ}C)$		
Repetitive Peak Surge Current	150	Α
(Square Wave, 20kHz)		
Nonrepetitive Peak Surge Current	500	Α
(Halfwave, 1 Phase, 60Hz)		
Maximum Power Dissipation	190	W
Avalanche Energy (See Figures 7 and 8)	50	mJ
Operating and Storage Temperature	-65 to 175	°C

**Electrical Specifications**  $T_C = 25^{\circ}C$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V <sub>F</sub>	I <sub>F</sub> = 75A	-	-	2.1	V
	I <sub>F</sub> = 75A, T <sub>C</sub> = 150°C	-	-	1.9	V
I <sub>R</sub>	V <sub>R</sub> = 1200V	-	-	250	μА
	V <sub>R</sub> = 1200V, T <sub>C</sub> = 150 <sup>o</sup> C	-	-	2	mA
t <sub>rr</sub>	I <sub>F</sub> = 1A, dI <sub>F</sub> /dt = 100A/μs	-	-	125	ns
	$I_F = 75A$ , $dI_F/dt = 100A/\mu s$	-	-	200	ns
ta	$I_F = 75A$ , $dI_F/dt = 100A/\mu s$	-	90	-	ns
t <sub>b</sub>	$I_F = 75A$ , $dI_F/dt = 100A/\mu s$	-	65	-	ns
$R_{\theta JC}$		-	-	0.8	°C/W

#### **DEFINITIONS**

 $V_F$  = Instantaneous forward voltage (pw = 300 $\mu$ s, D = 2%).

 $I_R$  = Instantaneous reverse current.

 $t_{rr}$  = Reverse recovery time summation of  $t_a + t_b$ .

t<sub>a</sub> = Time to reach peak reverse current (See Figure 6).

 $t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 6).

 $R_{\theta JC}$  = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

## **Typical Performance Curves**

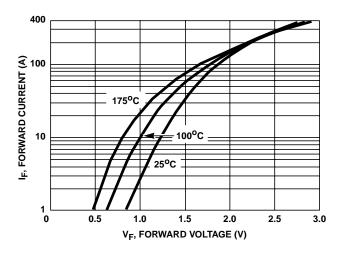


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

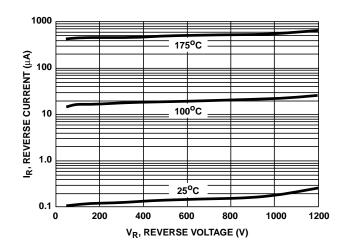


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

### Typical Performance Curves (Continued)

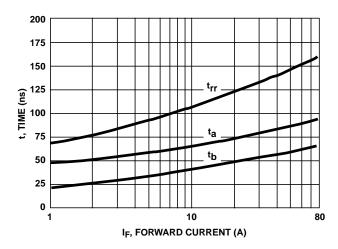
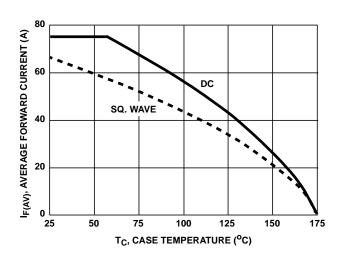


FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT



**FIGURE 4. CURRENT DERATING CURVE** 

#### Test Circuits and Waveforms

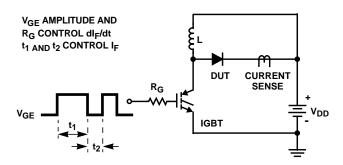


FIGURE 5. t<sub>rr</sub> TEST CIRCUIT

 $0 \xrightarrow{|f|} \frac{d|f|}{dt}$   $0.25 I_{RM}$ 

FIGURE 6. t<sub>rr</sub> WAVEFORMS AND DEFINITIONS

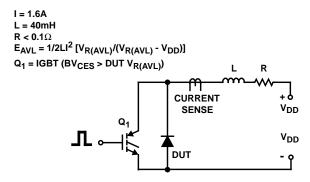


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

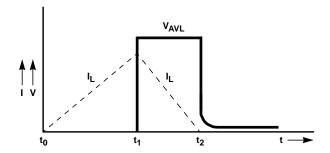


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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